

High-Frequency Hopping conductivity of Disordered 2D-system in the IQHE Regime

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High frequency (hf) conductivity in the form $\sigma^{hf} = \sigma_1^{hf} - i\sigma_2^{hf}$ was obtained from the measurement of Surface Acoustic Waves (SAW) attenuation and velocity ($f=30$ MHz) in GaAs/AlGaAs heterostructures ($n = 1.3 - 7 \cdot 10^{11} \text{ cm}^{-2}$). It has been shown that in the Integer Quantum Hall Effect (IQHE) regime for all the samples at magnetic fields corresponding to the middle of the Hall plateaus and $T=1.5$ K, $\sigma_1/\sigma_2 = 0.14 \pm 0.03$. The ratio $\sigma_1/\sigma_2 = 0.15$ points the case when the high-frequency hopping conductivity mechanism (electronic transition between the localized states formed by "tight" pairs) is valid [1]. Dependencies of σ_1 and σ_2 on temperature and magnetic field is analyzed width of the Landau band broadened by the impurity random potential is determined.

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INTRODUCTION

If one places a semiconducting heterostructure over a piezoelectric which SAW is being propagated, the SAW undergoes attenuation associated with the interaction of the electrons of heterostructure with the electric field of SAW. This is the basis of the acoustic method pioneered by Wixforth [2] for the investigation of GaAs/AlGaAs heterostructures. In the paper [3] it has been found that in a GaAs/AlGaAs heterostructure in the IQHE regime the acoustically measured conductivity σ^{hf} does not coincide with the σ^{dc} obtained from the direct-current measurements: $\sigma^{dc}=0$, whereas σ^{hf} has a finite value. This difference was explained by means of a conventional model of electrons being localized in the IQHE regime, therefore the conductivity mechanism for a direct current differs from that for an alternative current. For the localized electrons in the hopping conduction regime hf-conductivity can be expressed as a complex value: $\sigma^{hf} = \sigma_1^{hf} - i\sigma_2^{hf}$ [4]. Absorption coefficient of SAW, Γ , and the change of SAW velocity- $\Delta V/V$ -can be presented in the way:

$$\Gamma = 8.68 \frac{K^2}{2} kA \frac{(\frac{4\pi\sigma_1}{\varepsilon_s V})t(k)}{[1 + (\frac{4\pi\sigma_2}{\varepsilon_s V})t(k)]^2 + [(\frac{4\pi\sigma_1}{\varepsilon_s V})t(k)]^2}, \quad (1)$$

$$A = 8b(k)(\varepsilon_1 + \varepsilon_0)\varepsilon_s^2 \exp(-2k(a+d)),$$

$$\frac{\Delta V}{V} = \frac{K^2}{2} A \frac{(\frac{4\pi\sigma_2}{\varepsilon_s V})t(k) + 1}{[1 + (\frac{4\pi\sigma_2}{\varepsilon_s V})t(k)]^2 + [(\frac{4\pi\sigma_1}{\varepsilon_s V})t(k)]^2},$$

where K^2 is the electromechanical coupling coefficient of piezoelectric substrate, k and V are the SAW wavevector and the velocity respectively, a is the vacuum gap

width of 2DEG, d is the depth of the 2D-layer, ε_1 , ε_0 and ε_s are the dielectric constants of lithium niobate, vacuum and semiconductor respectively, b and t are complex function of a , d , ε_1 , ε_0 and ε_s .

The aim of the work is to determine $\text{Re}\sigma^{hf}(H,T)$ and $\text{Im}\sigma^{hf}(H,T)$ in IQHE regime from the Γ and $\Delta V/V$ of SAW measurements ($f=30$ MHz, $T=1.5-4.2$ K, H up to 7 T) and to analyze the 2D-electrons localization mechanism.

THE EXPERIMENTAL RESULTS AND DISCUSSION

Fig.1 illustrates the experimental dependencies of Γ and $\Delta V/V$ on H at $T=1.5$ K for the sample 1 ($n = 2.7 \cdot 10^{11} \text{ cm}^{-2}$). As long as Γ and $\Delta V/V$ are determined by the 2DEG conductivity (Eq.(1)), quantizing of the electro nspectrum in the magnetic field, leading to the SdH oscillations, results in similar peculiarities in Γ and $\Delta V/V$ of fig.1. Fig.2a presents the $\sigma_1(T)$ dependencies determined from Γ and $\Delta V/V$ (Fig.1) using Eq.(1) for $H=5.5$; 2.7 and 1.8 T ($\nu=2, 4, 6$ respectively), $\nu=nch/eH$ is the filling factor. Fig.2b shows the $\sigma_2(T)$ dependencies derived from Γ and $\Delta V/V$ for $H=5.5, 2.7$ and 1.8 T. Fig.3 illustrates the dependencies σ_1 and σ_2 on magnetic field near $H=5.5$ T ($\nu=2$) at different temperatures. In a number of papers (see f.e. [5]) devoted to the study of magnetoresistance in IQHE regime it was established that in IQHE plateau regions at low T the dominant conductivity mechanism is variable range hopping.

HF-conductivity in this case is determined by the two-site model and is associated with the electronic transition between localized states of "tight" pairs of impurities σ_1 . In this case the relation is valid:

$$\frac{Re\sigma}{Im\sigma} = \frac{\sigma_1}{\sigma_2} = \frac{\pi}{2} \ln \frac{\omega}{\omega_{ph}}, \quad (2)$$

where $\omega = 2\pi f$ is the frequency of SAW, ω_{ph} is the characteristic phonon frequency of the order of $10^{12} - 10^{13} sec^{-1}$. The calculation using Eq.(2) gives $\sigma_1/\sigma_2 = 0.15$ ($f=30$ MHz). For all samples it was experimentally found $\sigma_1/\sigma_2 = 0.14 \pm 0.03$ at $T=1.5K$ and H in the Hall plateaux middle. This fact allows one to suppose that the mechanism that determines the Γ and $\Delta V/V$ of SAW interacting with localized electrons is that of the hf hopping conductivity [1].

For the analysis of the dependencies $\sigma_1(H, T)$ and $\sigma_2(H, T)$ we supposed it to be determined by two mechanisms: hf-hopping on the localized states of impurities and thermal activation to the upper Landau band. The value of σ_2 is proportional to the number of "tight" pairs, which is changed with a thermal activation processes ($\sigma_2 = 0$ for delocalized electrons [3]). So the dependence $\sigma_2(H, T)$ reflects a change of number of these pairs.

The dependence $\sigma_1(H)$ is similar to behaviour of σ^{dc} when it makes SdH-oscillations, but $\sigma_1 > \sigma^{dc} = 0$. $\sigma_1(T)$ can be presented as a sum of two terms: $\sigma_1 = \sigma_1^h + \sigma_1^a$, where $\sigma_1^h = 0.11 \cdot \sigma_2^h$ is hf-conductivity, $\sigma_1^a = \sigma_0 \cdot \exp(-\Delta E/kT)$ is the conductivity on upper Landau band due to the electrons activated from the states on Fermi level where the activation energy $\Delta E = \hbar\omega_c/2 - C/2$, ($\hbar\omega_c$ is the cyclotron frequency, C is the Landau band

width). From the plotted dependence $\ln(\sigma_1 - \sigma_1^h)$ on $1/T$ the ΔE was found for $H=5.5, 2.7, 1.8T$. One can see (inset of Fig.2a) that ΔE is linear function of H with the slope $0.5\hbar\omega_c$ what allow to derive the width of Landau band, broadened, probably, by the impurity random potential; the width is appeared to be $C=2meV$.

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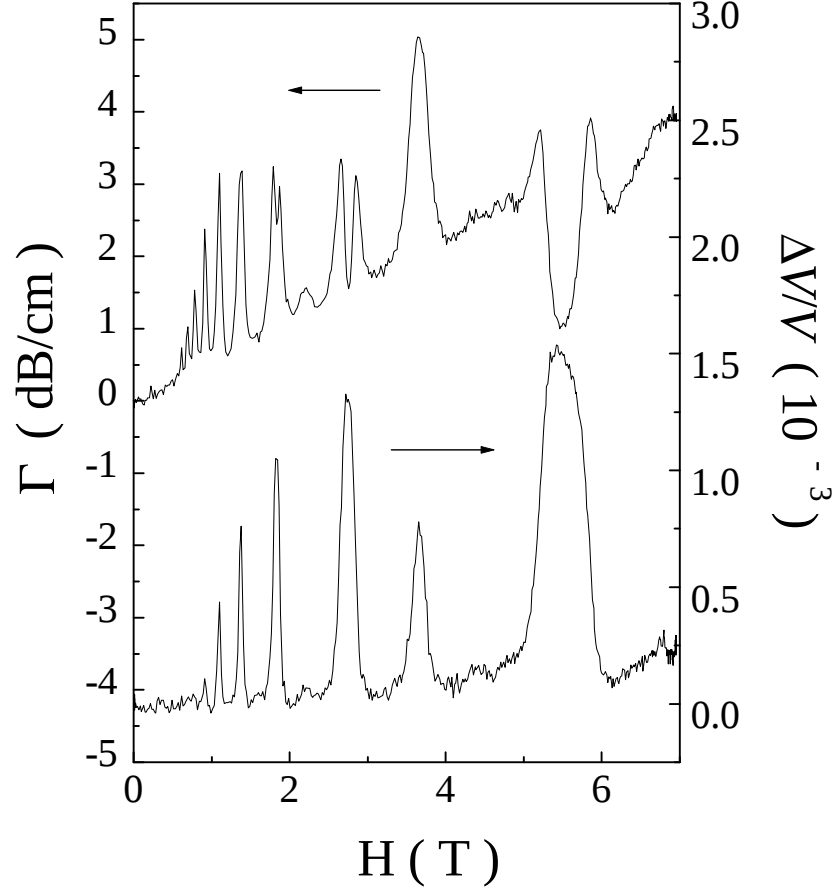


FIG. 1. The experimental dependence of Γ and $\Delta V/V$ on H at $T=1.5\text{K}$, ($f=30\text{MHz}$).

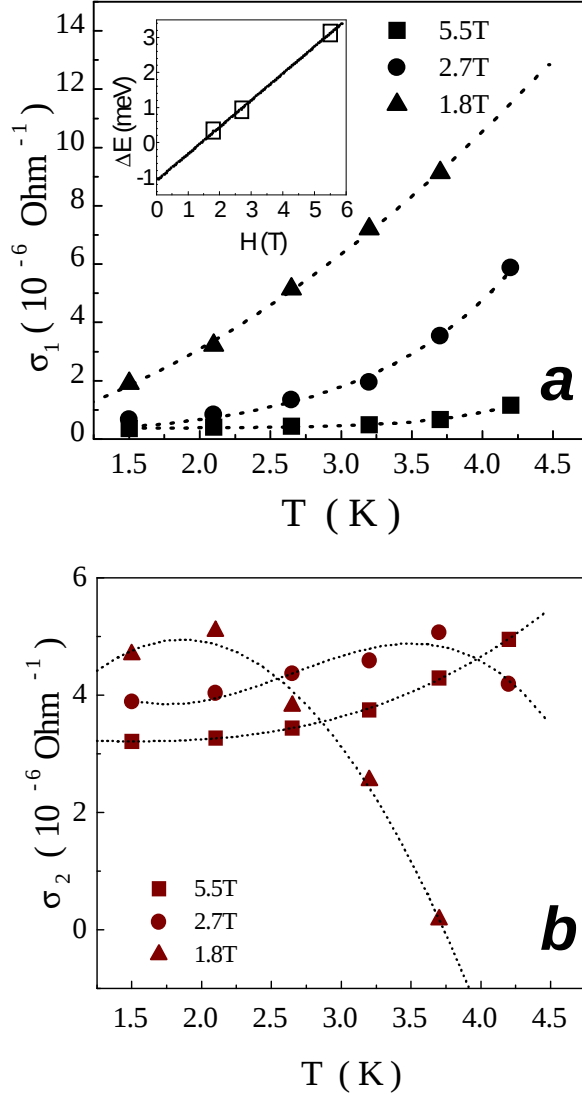


FIG. 2. (a) The dependence of $\sigma_1(T)$ near $\nu=2$; 4;6. Inset: Activation energy plotted vs. H . (b) The $\sigma_2(T)$ dependence near the filling factors $\nu=2$; 4; 6, ($f=30\text{MHz}$).

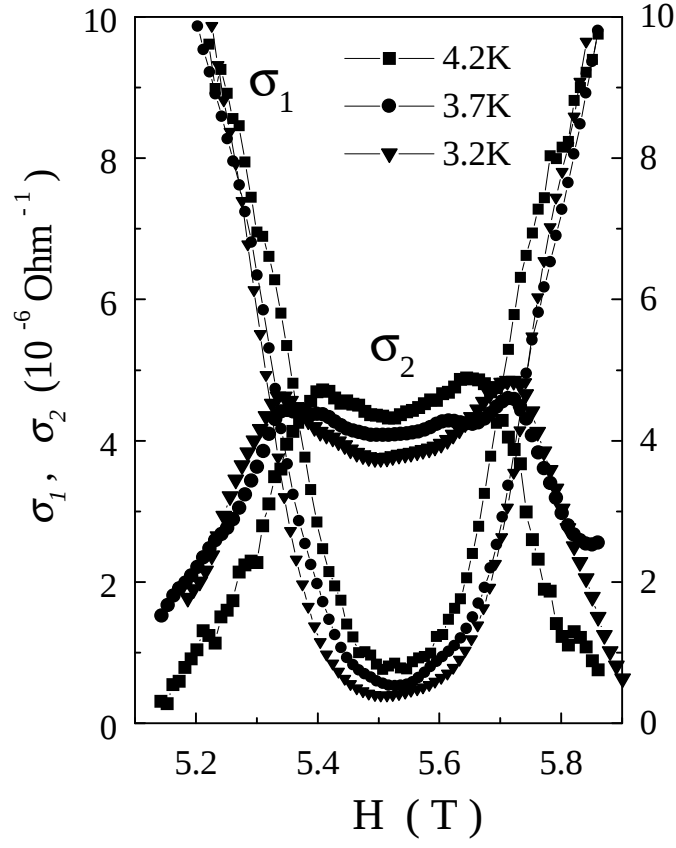


FIG. 3. The $\sigma_1(H)$ and $\sigma_2(H)$ at different temperatures near the filling factor $\nu=2$.